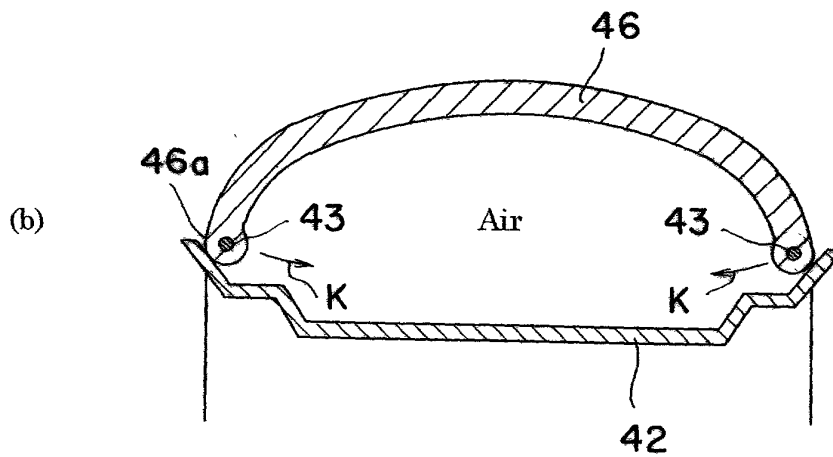
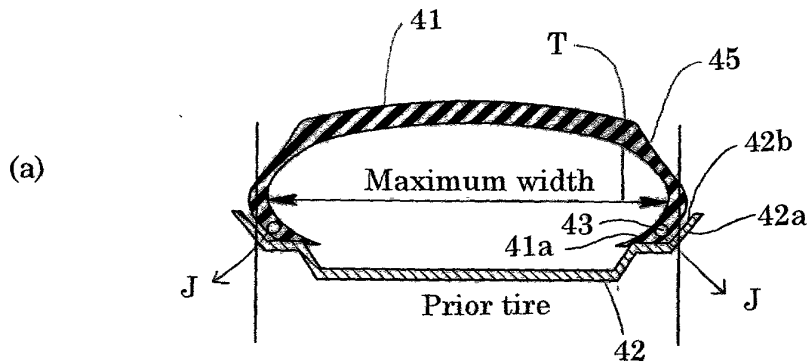


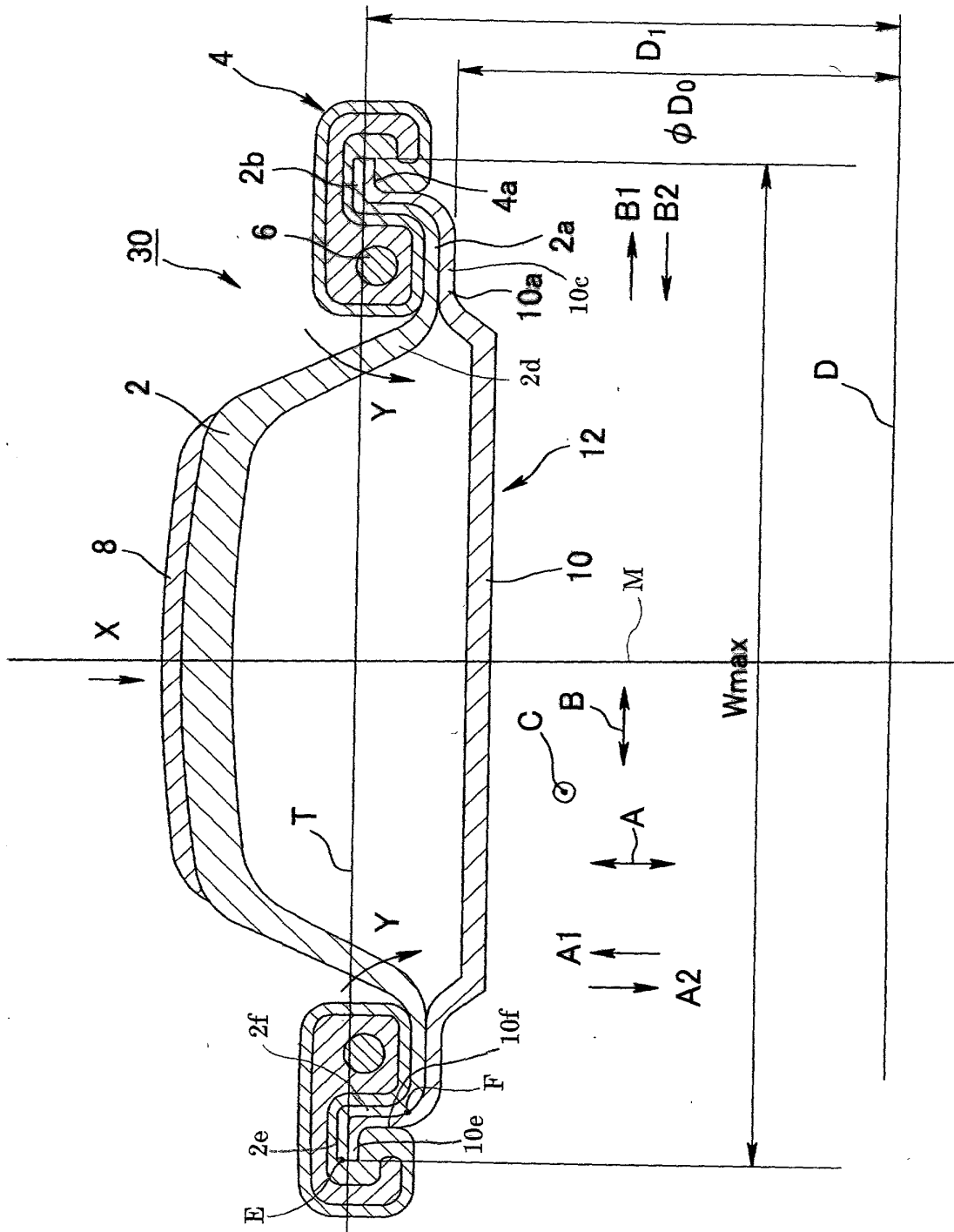
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【Fig.1】

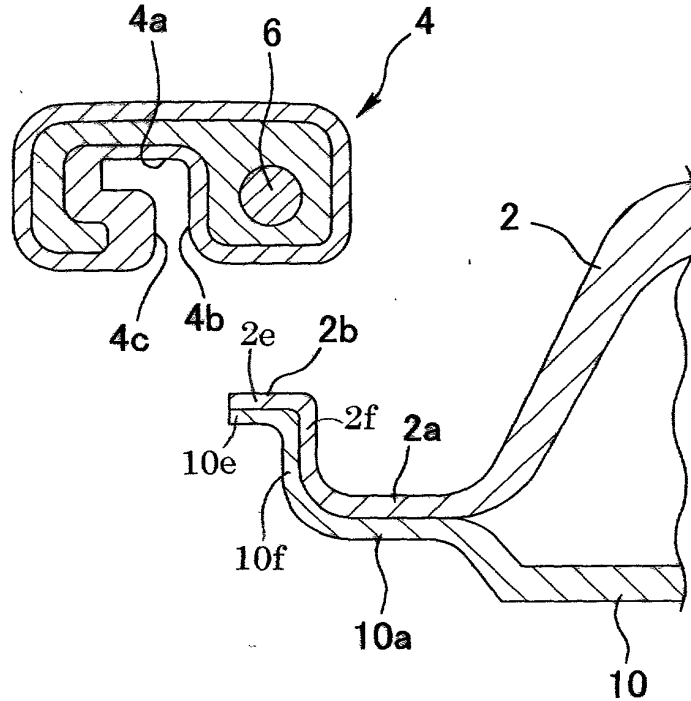


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【Fig.2】

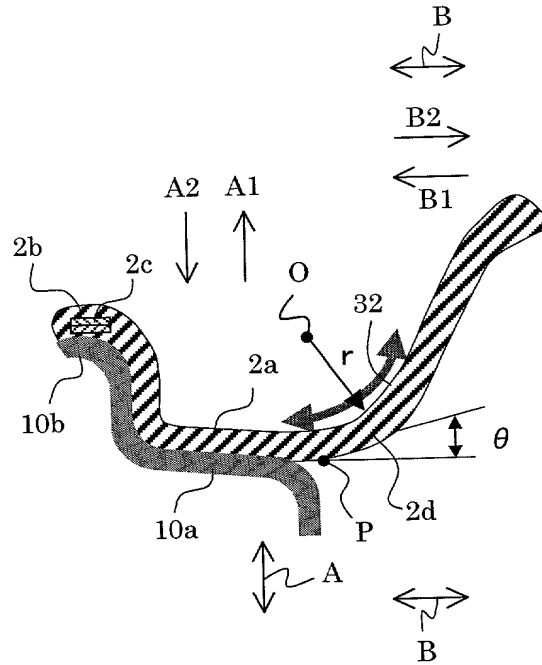


【Fig.3】



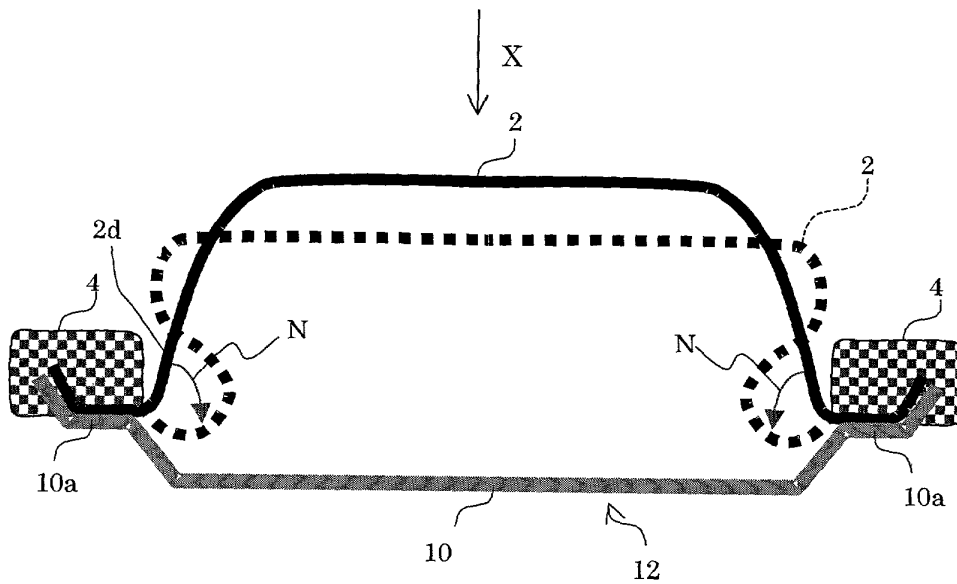
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【Fig.4】

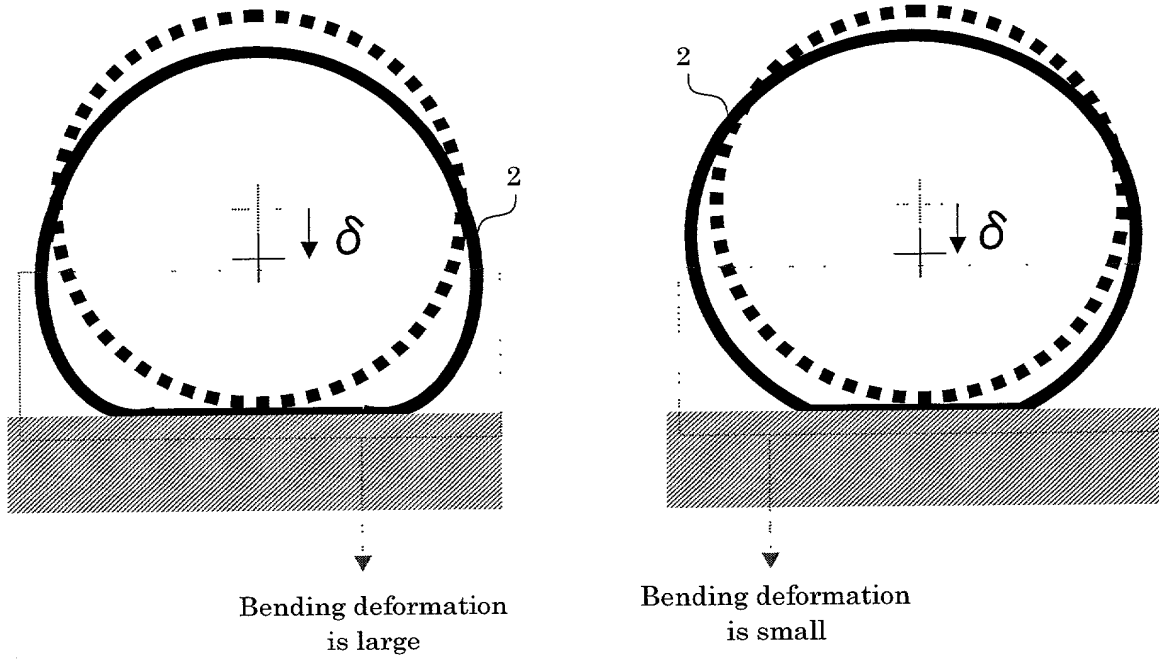


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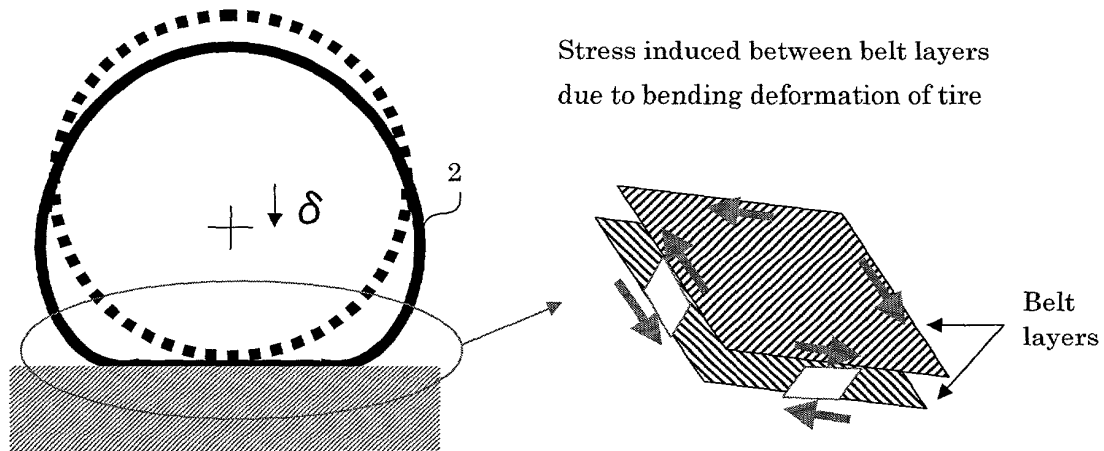
【Fig.5】



【Fig.6】

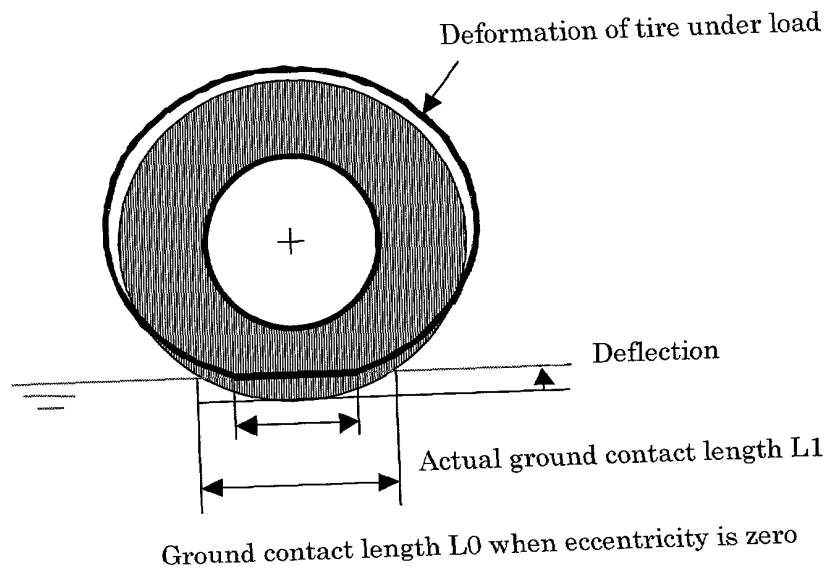


【Fig.7】



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【Fig.8】

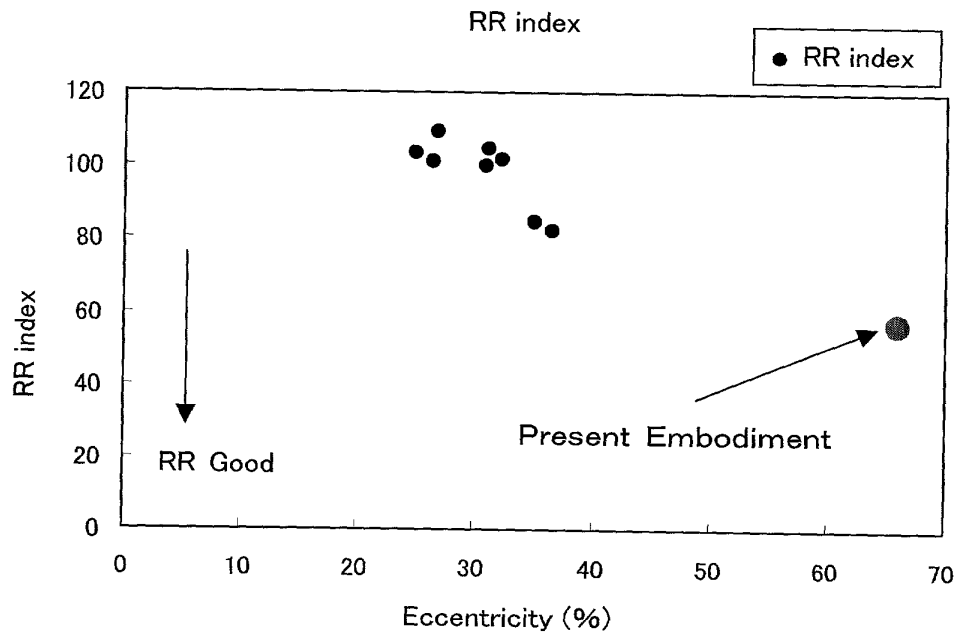


$$(\text{eccentricity}) = \frac{L0 - L1}{L0}$$

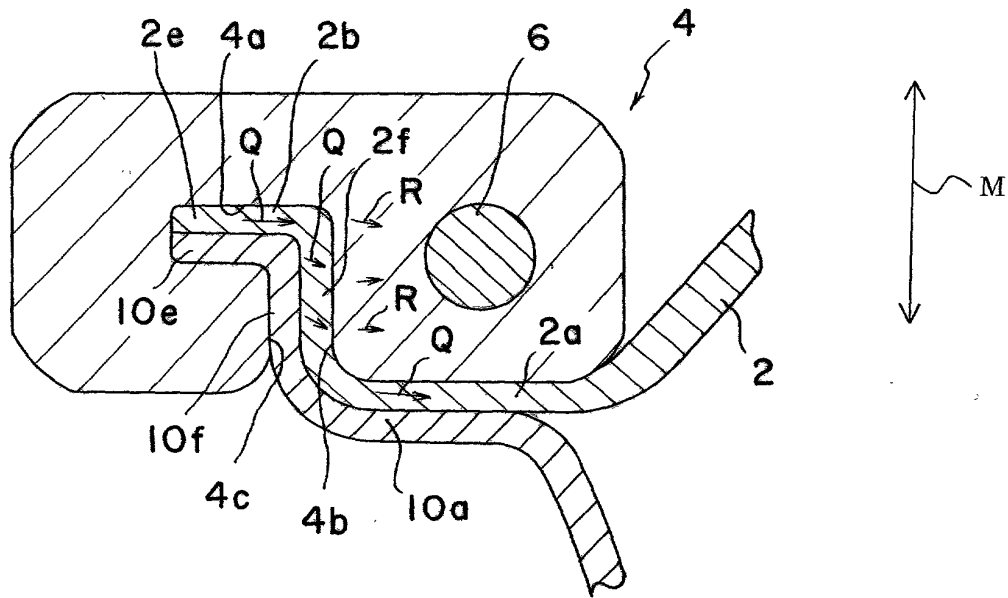
Actual ground contact length L1 is smaller than L0 (when eccentricity is zero) because of eccentricity.

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【Fig.9】



【Fig.10】



【Fig.11】

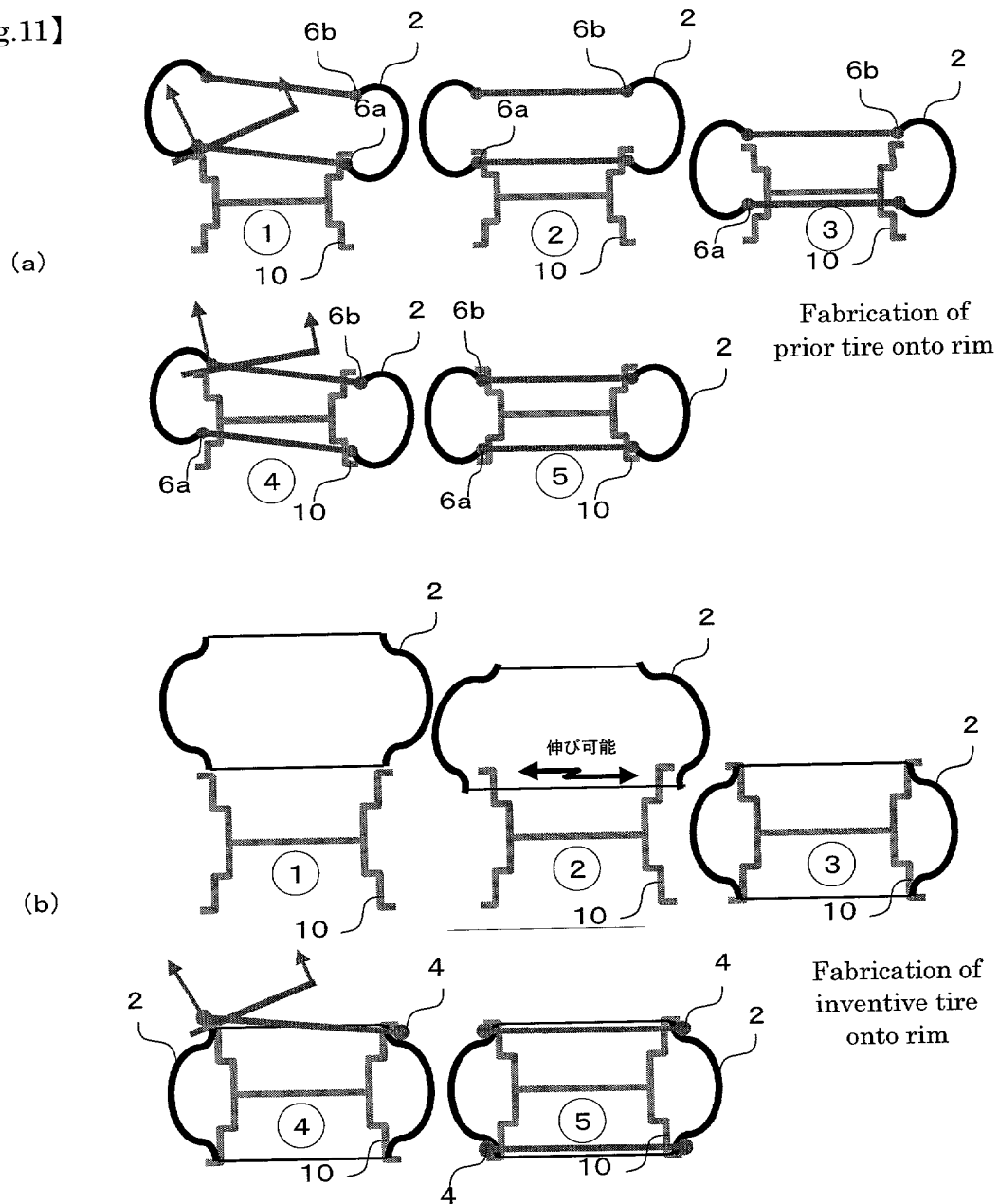
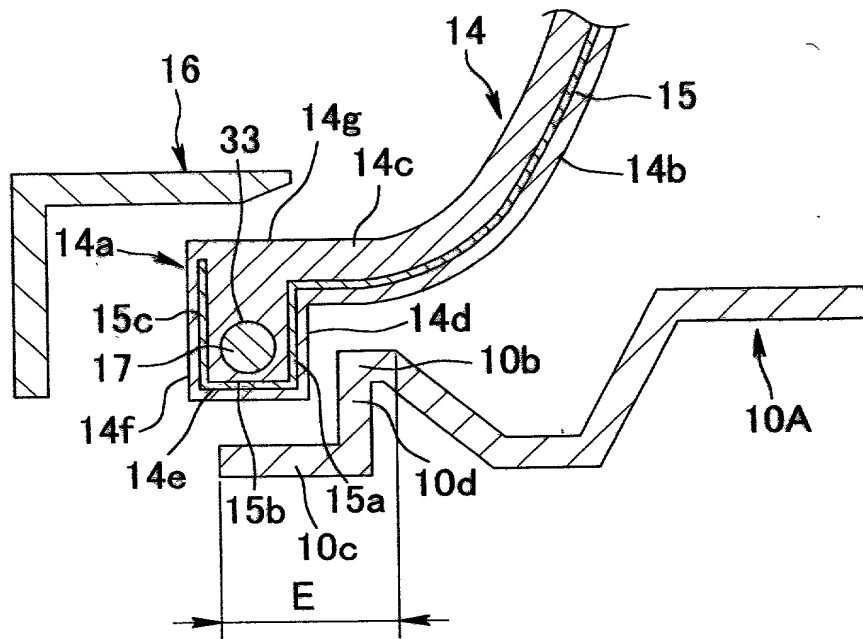


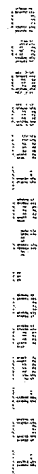
Diagram 30A is a cross-sectional view of a semiconductor device. It features a substrate 10 with a central layer 12A and side layers 10A, 10B, and 10C. A curved layer 14 with a top layer 15 is positioned above the central layer. The device is mounted on a base 16 with fasteners 17. Dimensions Wmax and D are indicated.

(a)

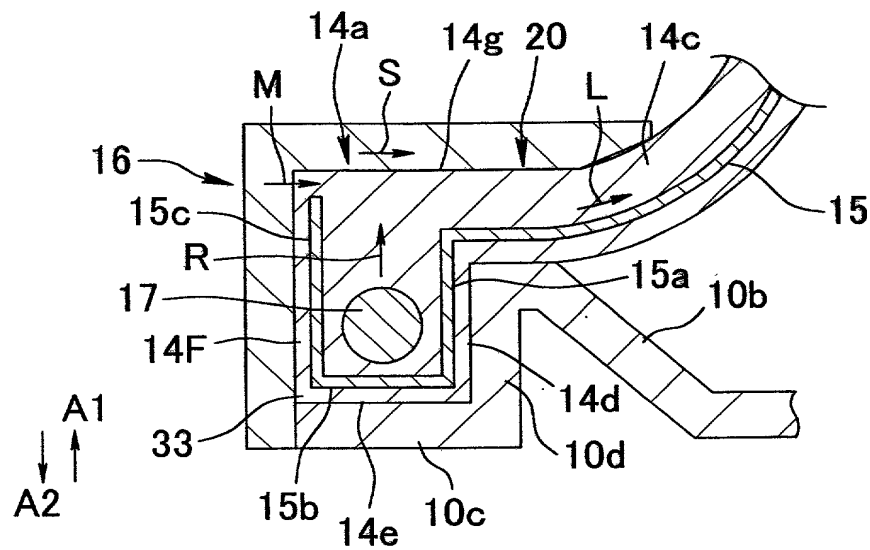
(b)

【Fig.14】



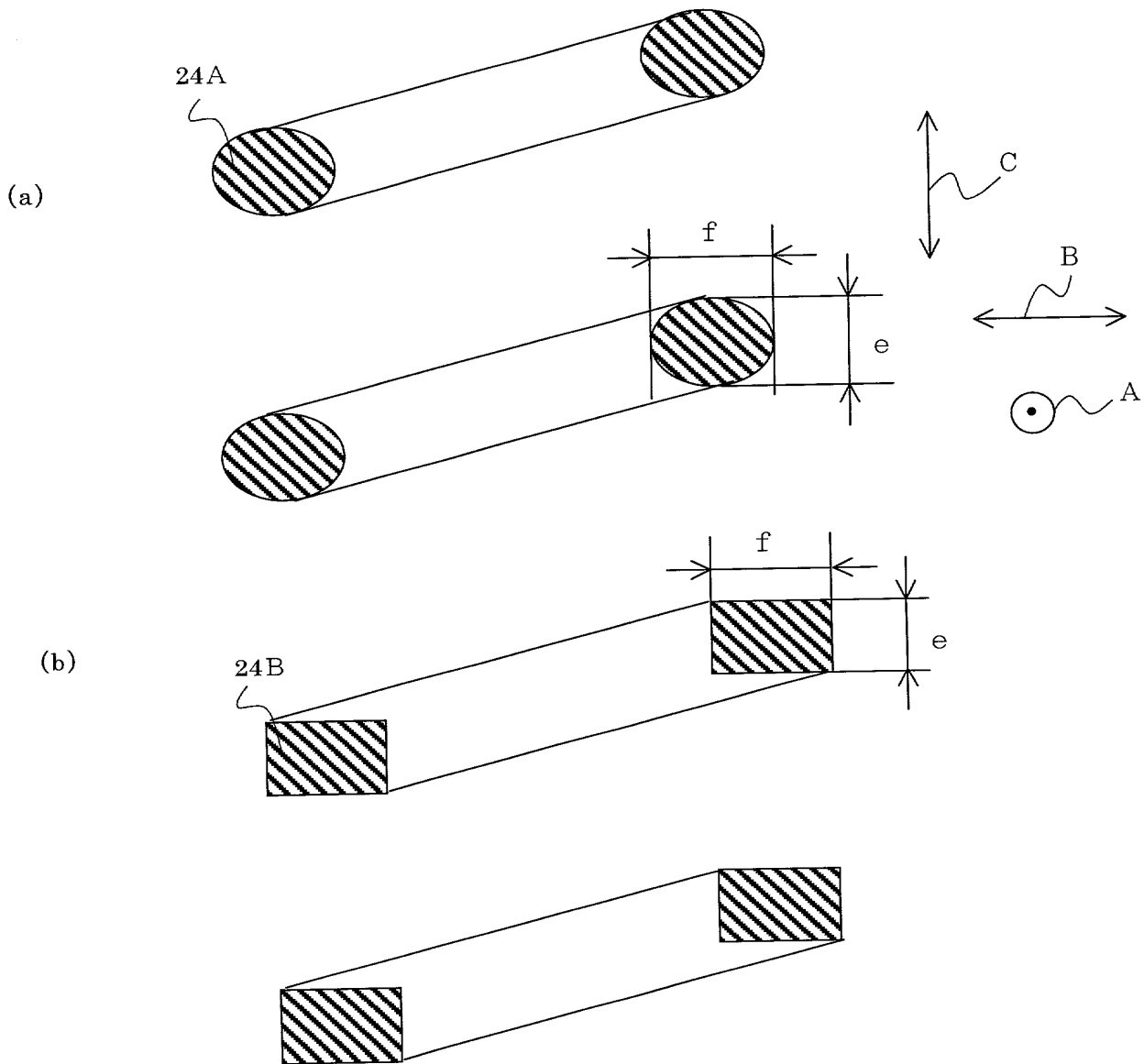


【Fig.18】

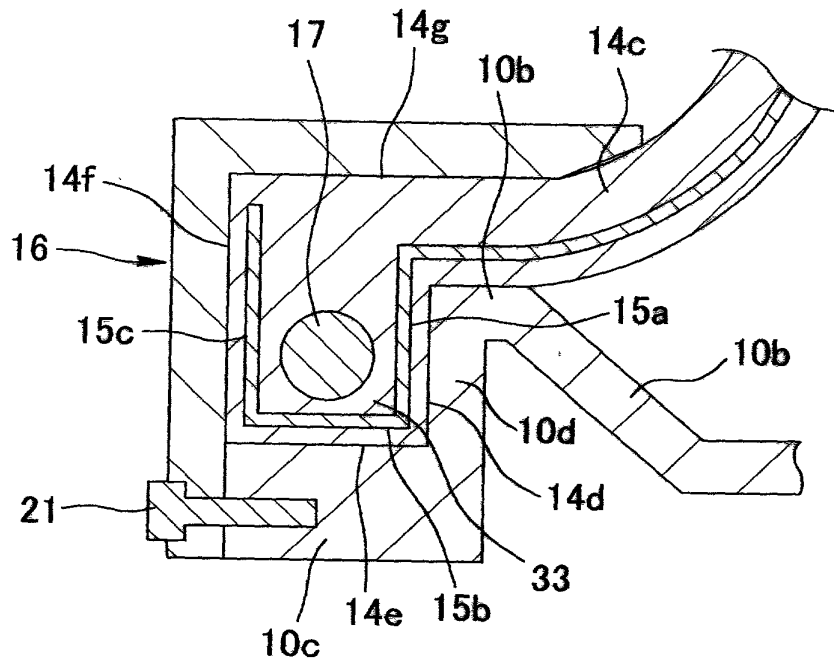


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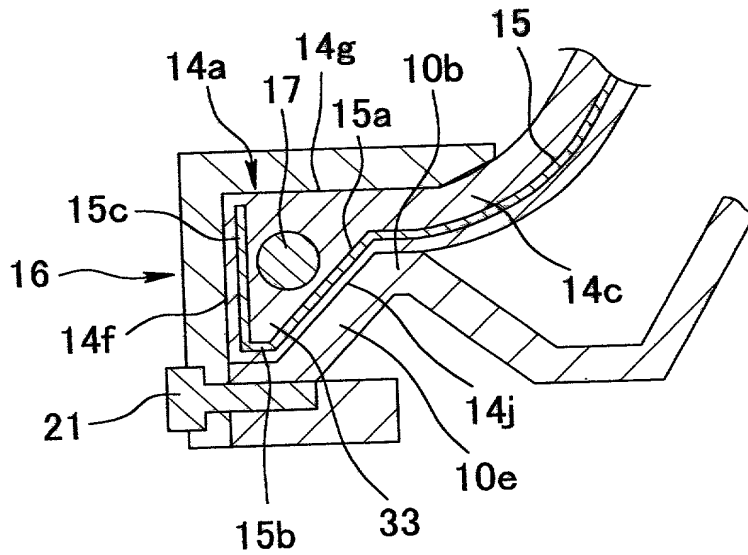
【Fig.19】



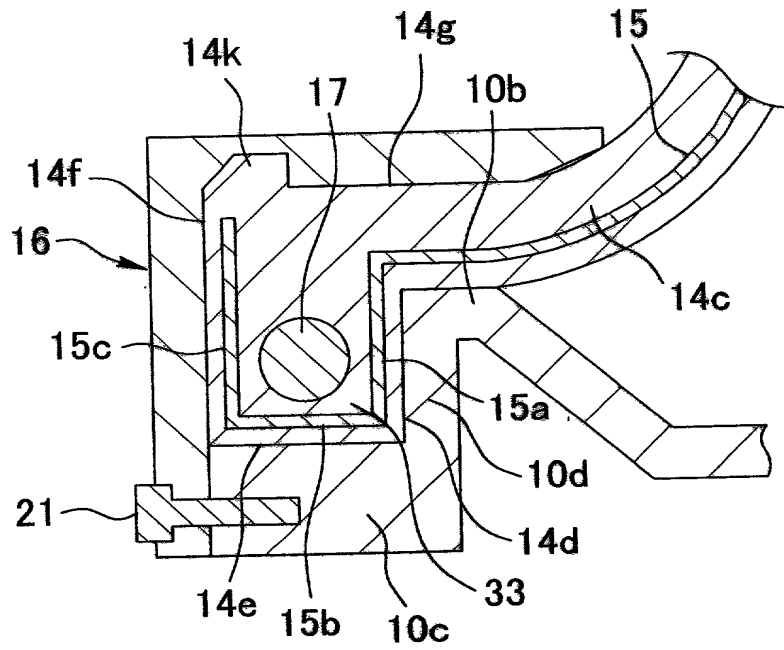
【Fig.20】



【Fig.21】



【Fig. 22】



【Fig.23】

